

## 1. General description

Silicon Carbide MOSFET in a TO263-7L plastic package, designed for high frequency, high efficiency systems.



AEC - Q101 Qualified



## 2. Features and benefits

- Kelvin source configuration
- Low on-resistance
- Fast switching speed
- 0V turn-off  $V_{GS}$  for simple gate driving
- 100% UIS Tested
- Easy to parallel
- RoHS compliant

## 3. Applications

- Automotive on board chargers
- Automotive DC-DC converters
- Automotive electric compressor motor drives
- HV battery management systems

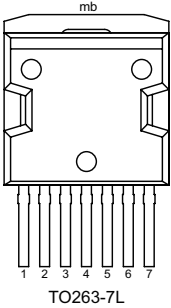
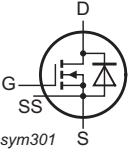
## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
<b>Absolute maximum rating</b>							
$V_{DS}$	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$		1200			V
$I_D$	drain current	$V_{GS} = 18\text{ V}; T_{mb} = 25\text{ °C}$		43			A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}, T_j = 175\text{ °C}$		234			W
$T_j$	junction temperature			-55 to 175			°C
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
<b>Static characteristics</b>							
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 15\text{ V}; I_D = 20\text{ A}; T_j = 25\text{ °C}$		-	75	-	mΩ
<b>Dynamic characteristics</b>							
$Q_{G(tot)}$	total gate charge	$I_D = 20\text{ A}; V_{DS} = 800\text{ V}; V_{GS} = -4\text{ V}/18\text{ V}; T_j = 25\text{ °C}$		-	63	-	nC
$Q_{GD}$	gate-drain charge			-	11	-	nC
<b>Source-drain diode</b>							
$Q_r$	recovered charge	$I_{SD} = 20\text{ A}; di/dt = 500\text{ A}/\mu\text{s}; V_{DS} = 400\text{ V}; T_j = 25\text{ °C}$		-	49	-	nC

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p style="text-align: center;">TO263-7L</p>	 <p style="text-align: center;">sym301</p>
2	SS	source sense		
3-7	S	source		
mb	D	mounting base; connected to drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WNSC2M75120B7-A	TO263-7L	WNSC2M75120B7-A6J	Reel	800	TO263P-7L	12-Jun-2023

## 7. Marking

Table 4. Marking codes

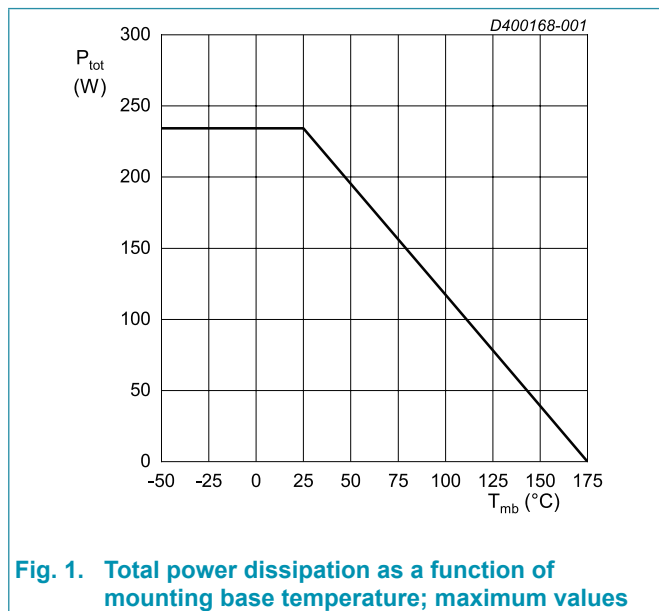
Type number	Marking codes
WNSC2M75120B7-A	WNSC2M 75120B7-A

## 8. Limiting values

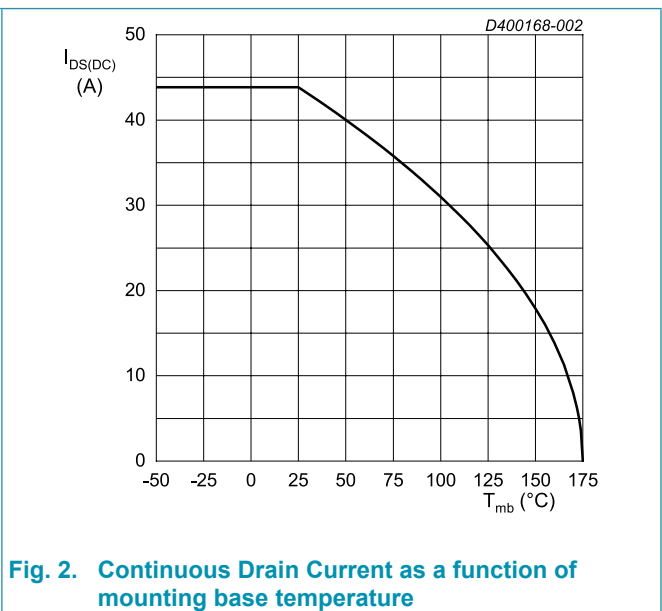
**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
$V_{DS}$	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$		1200	V
$V_{GS,max}$	gate-source voltage			-10 to 22	V
$V_{GS,op}$	gate-source voltage			-4 to 18	V
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}, T_j = 175\text{ °C}$		234	W
$I_D$	drain current	$V_{GS} = 18\text{ V}; T_{mb} = 25\text{ °C}$		43	A
		$V_{GS} = 18\text{ V}; T_{mb} = 100\text{ °C}$		30	A
$I_{DM}$	peak drain current	pulse width $t_p$ limited by $T_{jmax}$	Fig.17	86	A
$I_S$	continuous diode current	$V_{GS} = -4\text{ V}; T_{mb} = 25\text{ °C}$		40	A
$I_{SM}$	pulse diode current	$V_{GS} = -4\text{ V}$ ; pulse width $t_p$ limited by $T_{jmax}$		86	A
$E_{as}$	single pulse drain-to-source avalanche	$I_{AS} = 15\text{ A}; L = 1\text{ mH}; V_{DD} = 100\text{ V}; T_j = 25\text{ °C}$		113	mJ
$T_{stg}$	storage temperature			-55 to 175	°C
$T_j$	junction temperature			-55 to 175	°C
$T_{sld(M)}$	peak soldering temperature			260	°C



**Fig. 1. Total power dissipation as a function of mounting base temperature; maximum values**



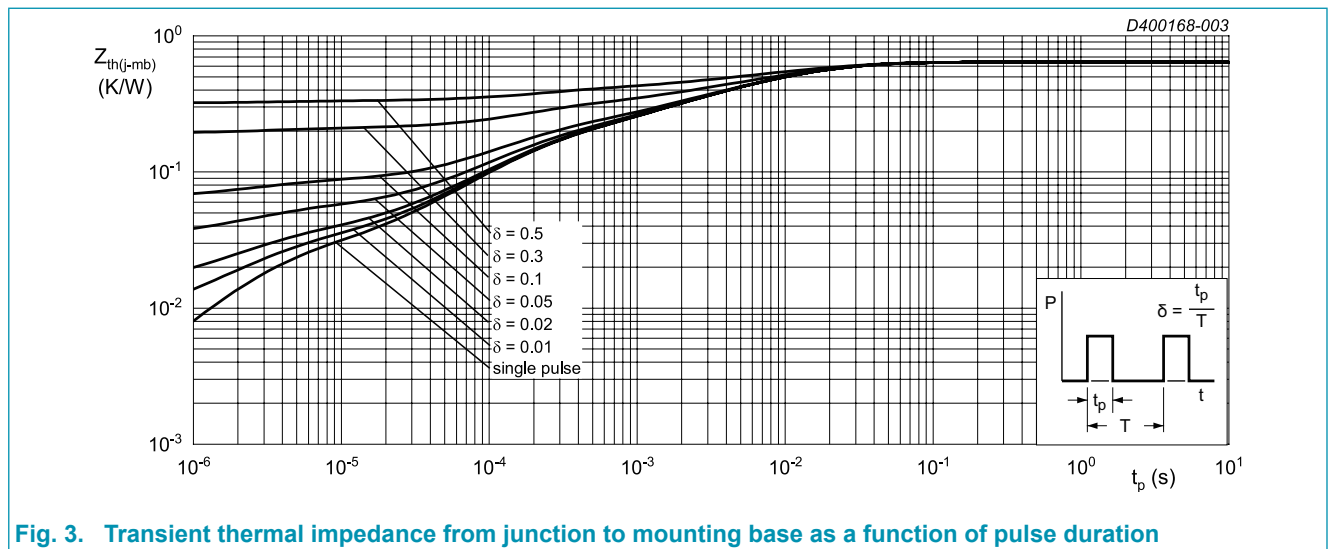
**Fig. 2. Continuous Drain Current as a function of mounting base temperature**

## 9. Thermal & Mechanical characteristics

**Table 6. Thermal & Mechanical characteristics**

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base			-	0.64	-	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		-	40	-	K/W

Note: It is recommended that a metal washer is inserted between screw head and mounting tab.  
Do not use self-tapping screws.  
Device is ESD sensitive. Handling precautions are recommended.

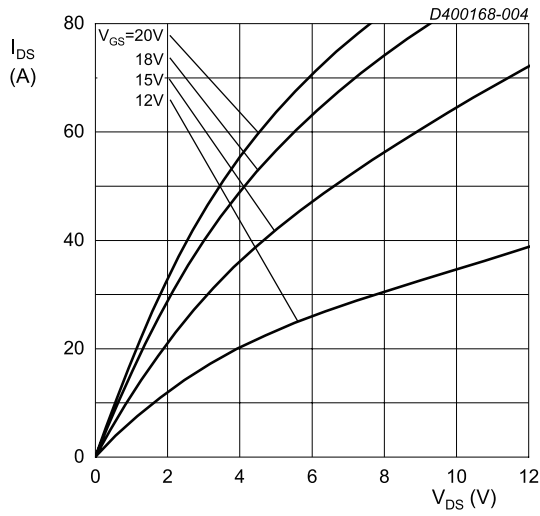


**Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse duration**

## 10. Characteristics

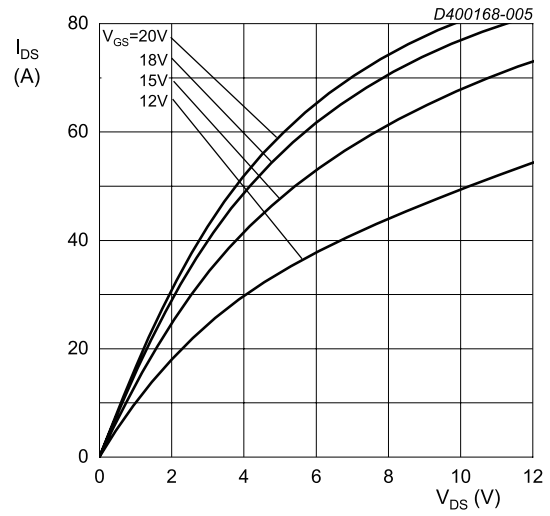
Table 7. Characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit	
<b>Static characteristics</b>								
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 100 \mu A; V_{GS} = 0 V; T_J = 25 \text{ }^\circ C$		1200	-	-	V	
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 5 \text{ mA}; V_{DS} = 10 \text{ V}; T_J = 25 \text{ }^\circ C$		1.8	2.2	3.5	V	
		$I_D = 5 \text{ mA}; V_{DS} = 10 \text{ V}; T_J = 175 \text{ }^\circ C$		-	1.5	-	V	
$I_{DSS}$	drain leakage current	$V_{DS} = 1200 \text{ V}; V_{GS} = 0 \text{ V}; T_J = 25 \text{ }^\circ C$		-	0.2	100	$\mu A$	
		$V_{DS} = 1200 \text{ V}; V_{GS} = 0 \text{ V}; T_J = 175 \text{ }^\circ C$		-	2	-	$\mu A$	
$I_{GSS}$	gate leakage current	$V_{GS} = 24 \text{ V}; V_{DS} = 0 \text{ V}; T_J = 25 \text{ }^\circ C$		-	10	100	nA	
		$V_{GS} = -12 \text{ V}; V_{DS} = 0 \text{ V}; T_J = 25 \text{ }^\circ C$		-	10	100	nA	
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 15 \text{ V}; I_D = 20 \text{ A}; T_J = 25 \text{ }^\circ C$		-	75	-	m $\Omega$	
		$V_{GS} = 18 \text{ V}; I_D = 20 \text{ A}; T_J = 25 \text{ }^\circ C$		-	64	90	m $\Omega$	
		$V_{GS} = 18 \text{ V}; I_D = 20 \text{ A}; T_J = 175 \text{ }^\circ C$		-	122	-	m $\Omega$	
$R_G$	gate resistance	$f = 1 \text{ MHz}; T_J = 25 \text{ }^\circ C$		-	2.5	-	$\Omega$	
$g_{fs}$	transconductance	$V_{DS} = 20 \text{ V}; I_D = 20 \text{ A}; T_J = 25 \text{ }^\circ C$		-	11.5	-	S	
<b>Dynamic characteristics</b>								
$Q_{G(tot)}$	total gate charge	$I_D = 20 \text{ A}; V_{DS} = 800 \text{ V}; V_{GS} = -4 \text{ V}/18 \text{ V}; T_J = 25 \text{ }^\circ C$		-	63	-	nC	
$Q_{GS}$	gate-source charge			-	25	-	nC	
$Q_{GD}$	gate-drain charge			-	11	-	nC	
$C_{iss}$	input capacitance	$V_{DS} = 1000 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_J = 25 \text{ }^\circ C$		-	1347	-	pF	
$C_{oss}$	output capacitance			-	58	-	pF	
$C_{rss}$	reverse transfer capacitance			-	4.6	-	pF	
$E_{oss}$	Coss stored energy			-	29	-	$\mu J$	
$t_{d(on)}$	turn-on delay time	$V_{DS} = 800 \text{ V}; V_{GS} = -4 \text{ V}/18 \text{ V}; R_{G(ext)} = 5.1 \text{ } \Omega; I_D = 20 \text{ A}; L = 300 \text{ } \mu H; T_J = 25 \text{ }^\circ C$		-	17	-	ns	
$t_r$	rise time			-	7	-	ns	
$t_{d(off)}$	turn-off delay time			-	35	-	ns	
$t_f$	fall time			-	15	-	ns	
$E_{on}$	turn-on energy <small>(Body Diode FWD)</small>			Fig.20	-	97	-	$\mu J$
$E_{off}$	turn-off energy <small>(Body Diode FWD)</small>			Fig.20	-	66	-	$\mu J$
<b>Source-drain diode</b>								
$V_{SD}$	source-drain voltage	$V_{GS} = 0 \text{ V}; I_{SD} = 10 \text{ A}; T_J = 25 \text{ }^\circ C$		-	3.2	-	V	
		$V_{GS} = -4 \text{ V}; I_{SD} = 10 \text{ A}; T_J = 25 \text{ }^\circ C$		-	4.8	-	V	
		$V_{GS} = -4 \text{ V}; I_{SD} = 10 \text{ A}; T_J = 175 \text{ }^\circ C$		-	4.2	-	V	
$t_{rr}$	reverse recovery time	$I_{SD} = 20 \text{ A}; di/dt = 500 \text{ A}/\mu s; V_{DS} = 400 \text{ V}; T_J = 25 \text{ }^\circ C$		-	21	-	ns	
$Q_r$	recovered charge			-	49	-	nC	
$I_{rrm}$	reverse recovery current			-	4.25	-	A	



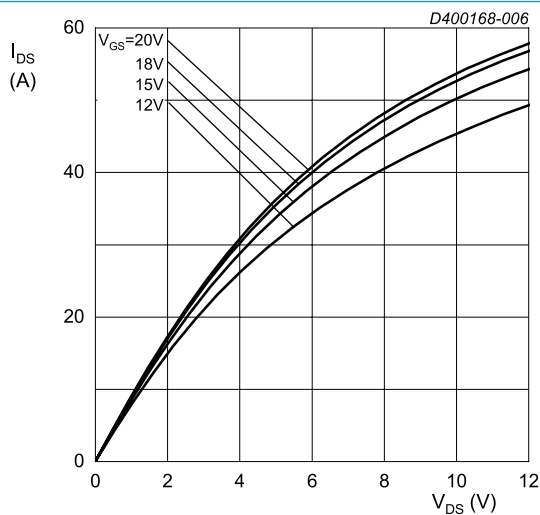
$T_j = -55\text{ °C}; t_p < 200\ \mu\text{s}$

**Fig. 4. Output characteristics; drain current as a function of drain-source voltage; typical values**



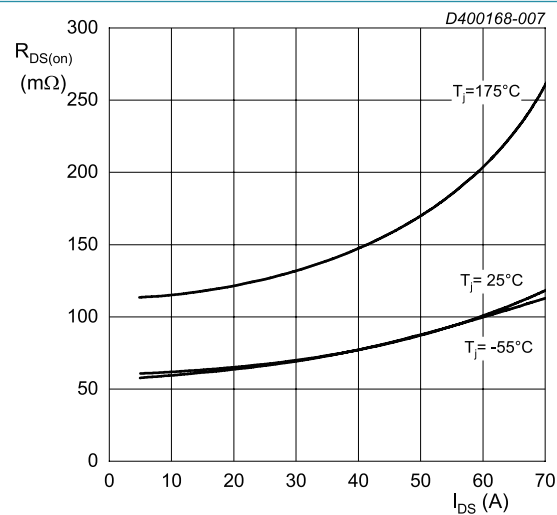
$T_j = 25\text{ °C}; t_p < 200\ \mu\text{s}$

**Fig. 5. Output characteristics; drain current as a function of drain-source voltage; typical values**



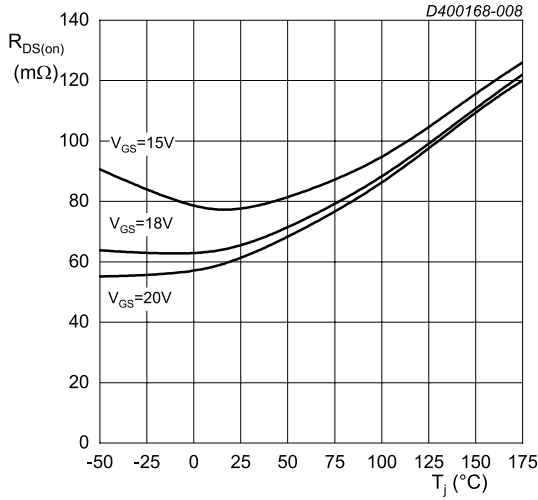
$T_j = 175\text{ °C}; t_p < 200\ \mu\text{s}$

**Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values**

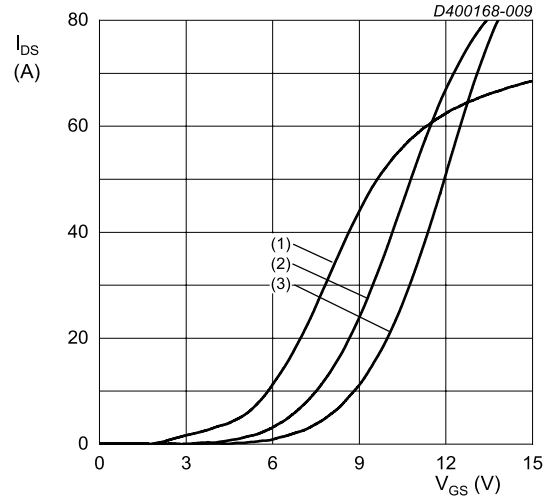


$V_{GS} = 18\text{ V}; t_p < 200\ \mu\text{s}$

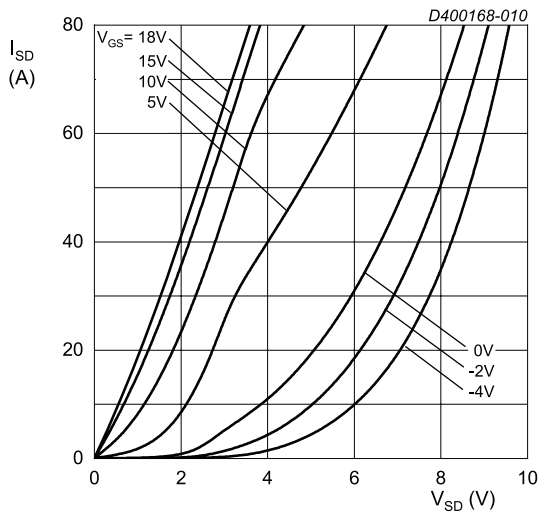
**Fig. 7. Drain-source on-state resistance as a function of drain current; typical values**



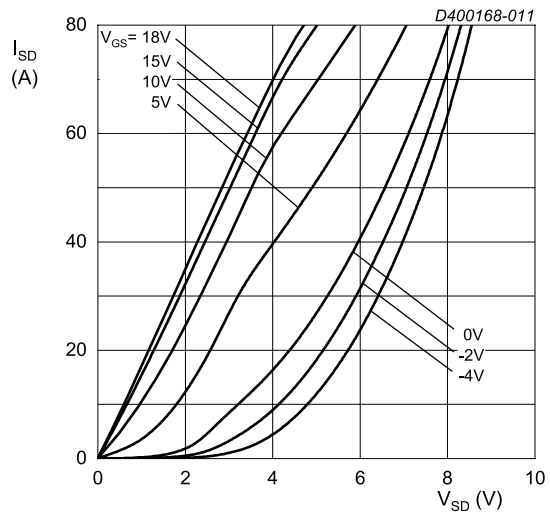
$I_{DS} = 20 A; t_p < 200 \mu s$   
**Fig. 8. Drain-source on-state resistance as a function of junction temperature**



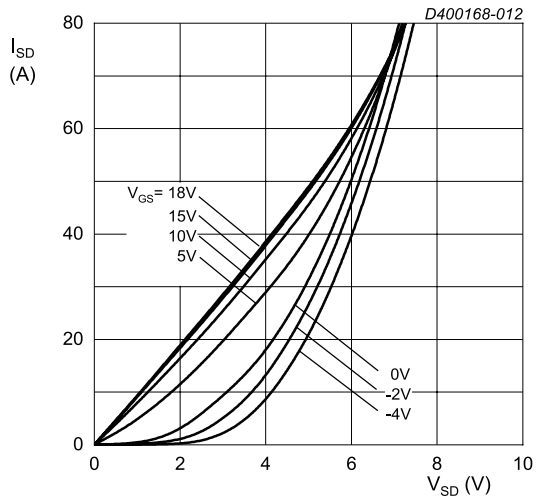
$V_{DS} = 20 V; t_p < 200 \mu s$   
 (1)  $T_j = 175^{\circ}C$   
 (2)  $T_j = 25^{\circ}C$   
 (3)  $T_j = -55^{\circ}C$   
**Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values**



$T_j = -55^{\circ}C; t_p < 200 \mu s$   
**Fig. 10. Body diode forward characteristics; typical values**

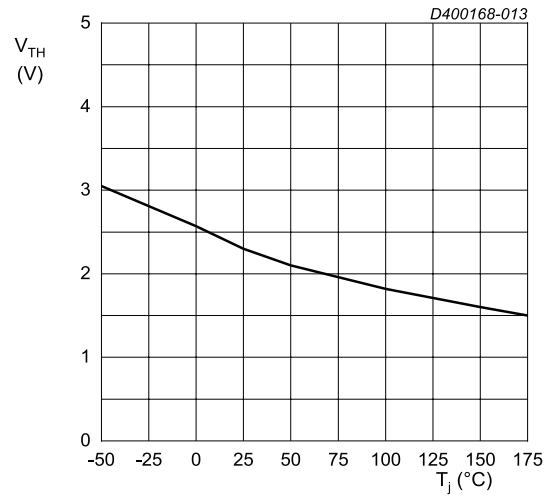


$T_j = 25^{\circ}C; t_p < 200 \mu s$   
**Fig. 11. Body diode forward characteristics; typical values**



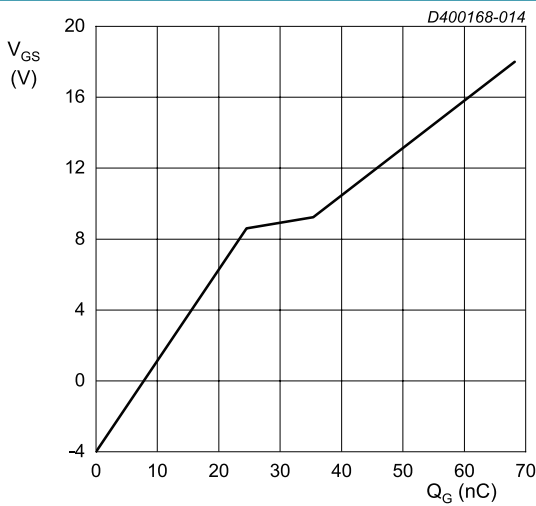
$T_j = 175\text{ }^\circ\text{C}$ ;  $t_p < 200\text{ }\mu\text{s}$

Fig. 12. Body diode forward characteristics; typical values



$V_{DS} = 10\text{ V}$ ;  $I_{DS} = 5\text{ mA}$

Fig. 13. Threshold voltage as a function of junction temperature



$I_{DS} = 20\text{ A}$ ;  $I_{GS} = 0.1\text{ mA}$ ;  $V_{DS} = 800\text{ V}$ ;  $T_j = 25\text{ }^\circ\text{C}$

Fig. 14. Gate-source voltage as a function of gate charge; typical values

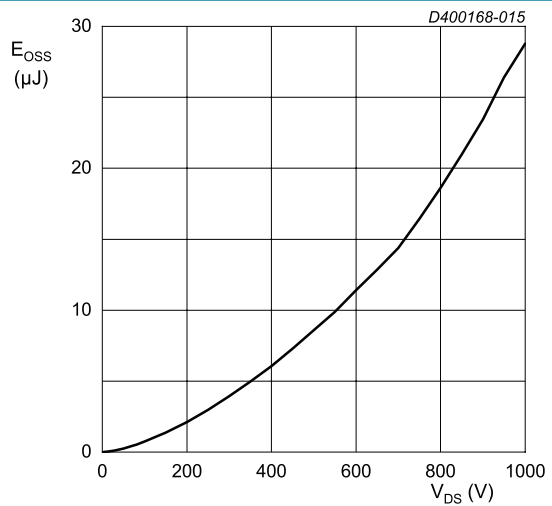
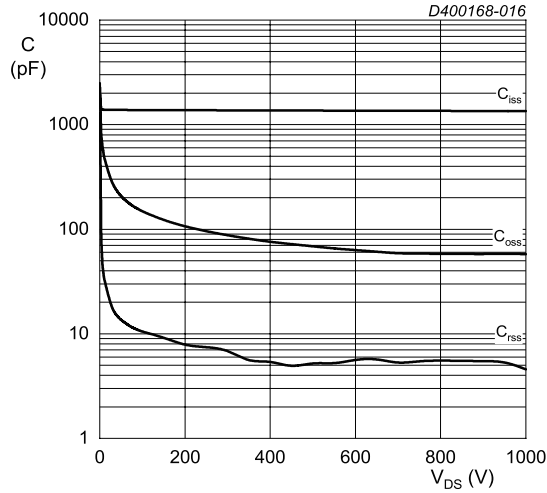


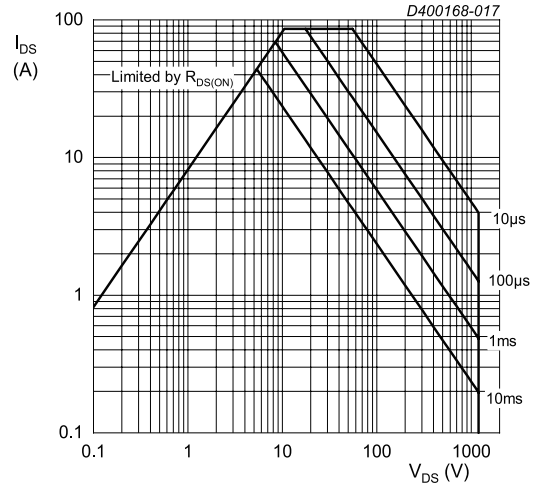
Fig. 15. Output capacitor stored energy as a function of drain-source voltage





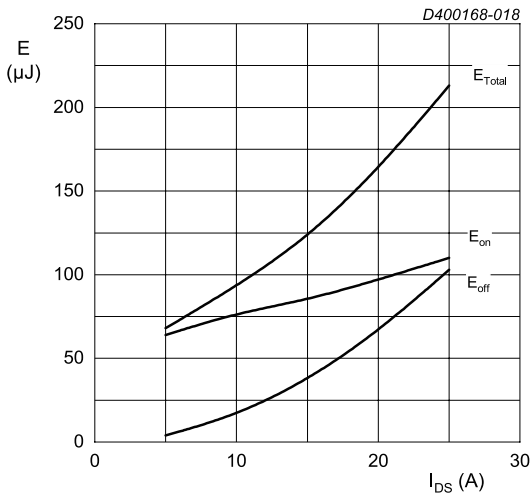
V<sub>DS</sub> = 0 - 1000 V  
 T<sub>j</sub> = 25 °C; V<sub>AC</sub> = 25 mV; f = 1 MHz

Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



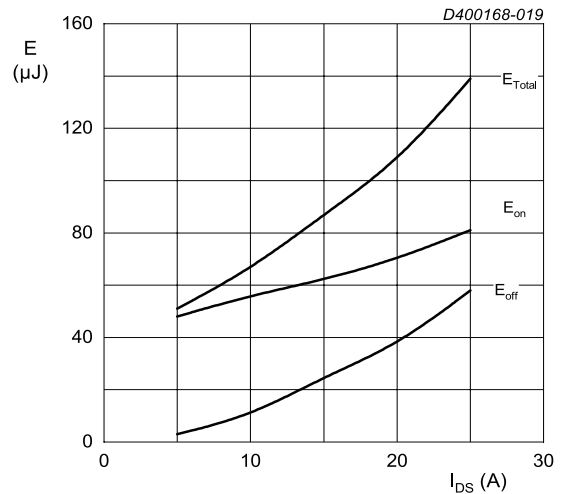
T<sub>j</sub> = 25 °C; D = 0  
 Parameter: t<sub>p</sub>

Fig. 17. Forward bias safe operating area



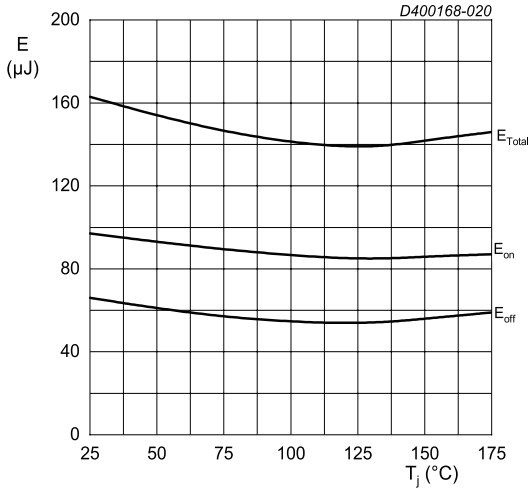
T<sub>j</sub> = 25 °C; V<sub>DD</sub> = 800 V; R<sub>G(ext)</sub> = 5.1 Ω;  
 V<sub>GS</sub> = -4 V/18 V; L = 300 μH  
 FWD = WNSC2M75120B7-A

Fig. 18. Clamped Inductive Switching Energy as a function of drain current



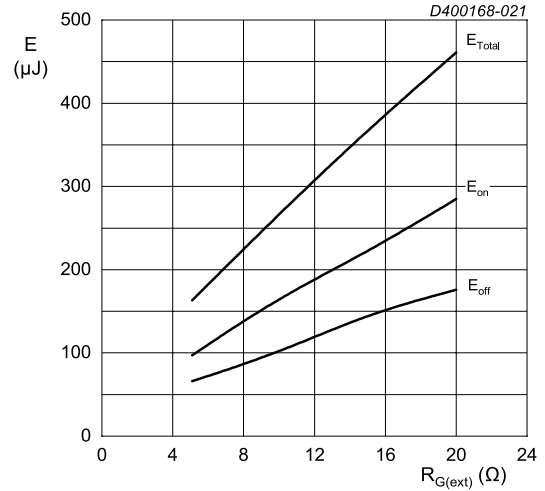
T<sub>j</sub> = 25 °C; V<sub>DD</sub> = 600 V; R<sub>G(ext)</sub> = 5.1 Ω;  
 V<sub>GS</sub> = -4 V/18 V; L = 300 μH  
 FWD = WNSC2M75120B7-A

Fig. 19. Clamped Inductive Switching Energy as a function of drain current



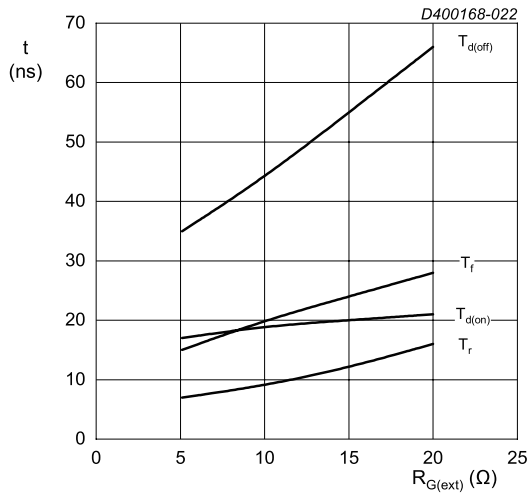
I<sub>DS</sub> = 20 A; V<sub>DD</sub> = 800 V; R<sub>G(ext)</sub> = 5.1 Ω;  
V<sub>GS</sub> = -4 V/18 V; L = 300 μH  
FWD = WNSC2M75120B7-A

**Fig. 20. Clamped Inductive Switching Energy as a function of junction temperature**



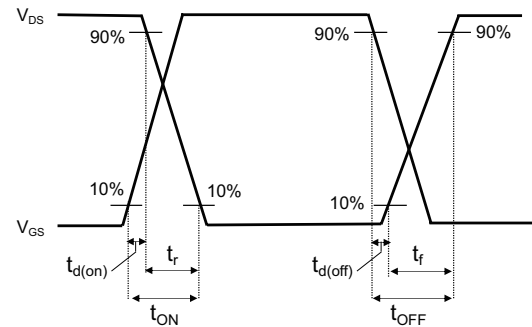
T<sub>j</sub> = 25 °C; V<sub>DD</sub> = 800 V; I<sub>DS</sub> = 20 A; V<sub>GS</sub> = -4 V/18 V  
FWD = WNSC2M75120B7-A; L = 300 μH

**Fig. 21. Clamped Inductive Switching Energy as a function of external gate resistance**



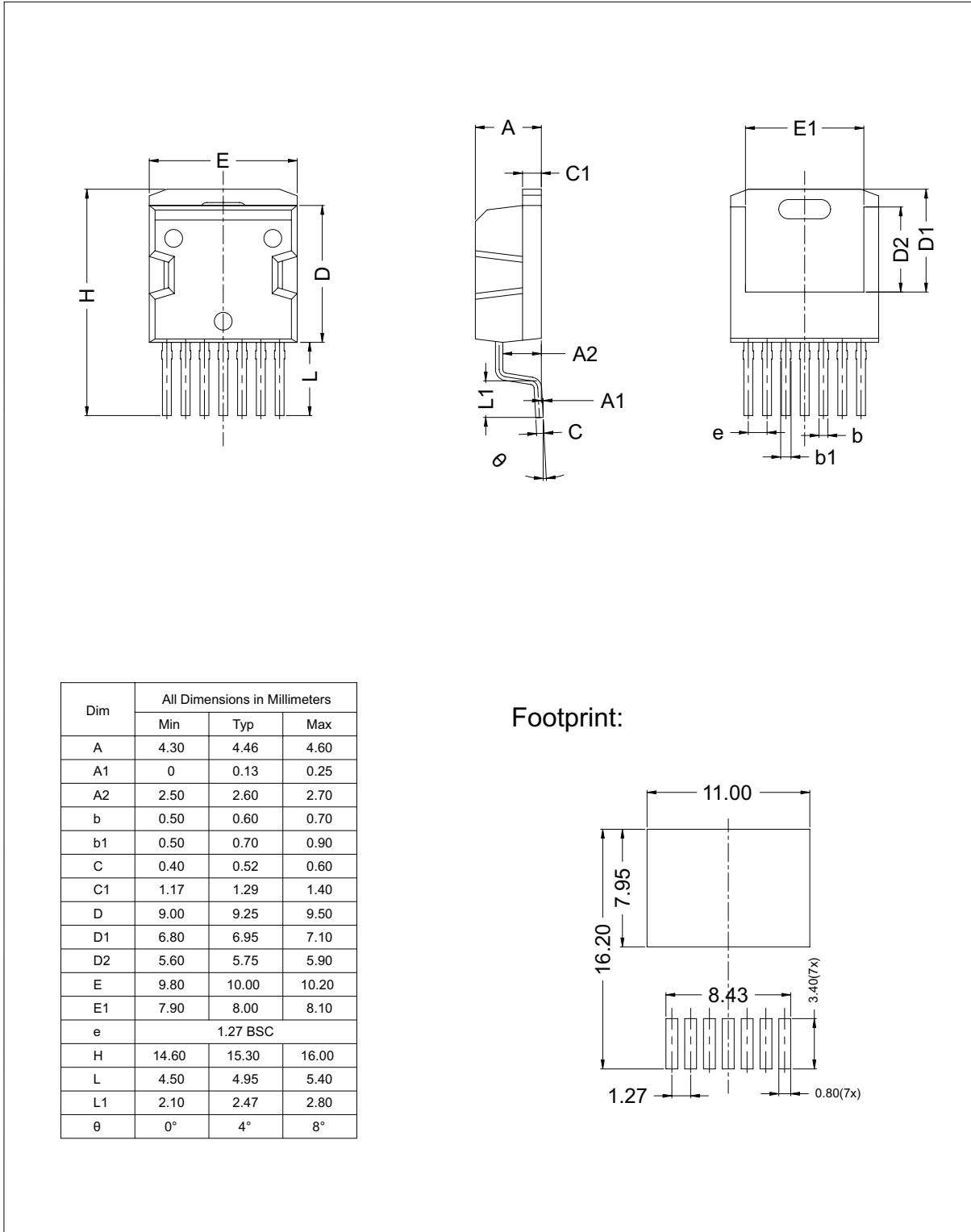
T<sub>j</sub> = 25 °C; V<sub>DD</sub> = 800 V; I<sub>DS</sub> = 20 A; V<sub>GS</sub> = -4 V/18 V  
FWD = WNSC2M75120B7-A; L = 300 μH

**Fig. 22. Switching time as a function of external gate resistance**



**Fig. 23. Switching time definition**

### 11. Package outline



## 12. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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